



MMDT4146

COMPLEMENTARY NPN / PNP SMALL SIGNAL SURFACE MOUNT TRANSISTOR

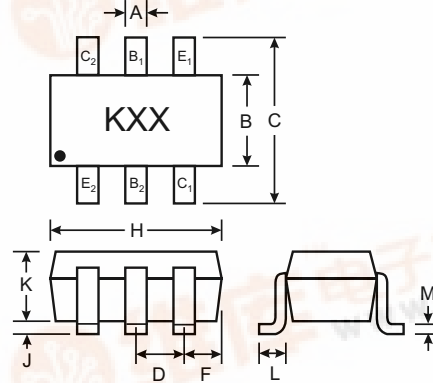
NEW PRODUCT

Features

- Complementary Pair
- One 4124-Type NPN,
One 4126-Type PNP
- Epitaxial Planar Die Construction
- Ideal for Medium Power Amplification and Switching
- Ultra-Small Surface Mount Package

Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: K12
- Weight: 0.006 grams (approx.)



E₁, B₁, C₁ = PNP4126 Section
E₂, B₂, C₂ = NPN4124 Section

SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings, NPN 4124 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	NPN 4124 Section	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6.0	V
Collector Current - Continuous (Note 1)	I _C	200	mA
Power Dissipation (Note 1, 2)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	K/W

Maximum Ratings, PNP 4126 Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	PNP 4126 Section	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-40	V
Emitter-Base Voltage	V _{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I _C	-200	mA
Power Dissipation (Note 1, 2)	P _d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	R _{θJA}	625	K/W

- Notes:
1. Valid provided that terminals are kept at ambient temperature. Total device dissipation.
 2. Maximum combined dissipation.



Electrical Characteristics, NPN 4124 Section@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	30	—	V	I _C = 10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	25	—	V	I _C = 1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5.0	6.0	V	I _E = 10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	50	nA	V _{CB} = 20V, I _E = 0V
Emitter Cutoff Current	I _{EBO}	—	50	nA	V _{EB} = 3.0V, I _C = 0V
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h _{FE}	120 60	360 —	—	I _C = 2.0mA, V _{CE} = 1.0V I _C = 50mA, V _{CE} = 1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	0.30	V	I _C = 50mA, I _B = 5.0mA
Base- Emitter Saturation Voltage	V _{BE(SAT)}	—	0.95	V	I _C = 50mA, I _B = 5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.0	pF	V _{CB} = 5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	8.0	pF	V _{EB} = 0.5V, f = 1.0MHz, I _C = 0
Small Signal Current Gain	h _{fe}	120	480	—	V _{CE} = 1.0V, I _C = 2.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	300	—	MHz	V _{CE} = 20V, I _C = 10mA, f = 100MHz

Electrical Characteristics, PNP 4126 Section@ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	V _{(BR)CBO}	-25	—	V	I _C = -10μA, I _E = 0
Collector-Emitter Breakdown Voltage	V _{(BR)CEO}	-25	—	V	I _C = -1.0mA, I _B = 0
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	-4.0	—	V	I _E = -10μA, I _C = 0
Collector Cutoff Current	I _{CBO}	—	-50	nA	V _{CB} = -20V, I _E = 0V
Emitter Cutoff Current	I _{EBO}	—	-50	nA	V _{EB} = -3.0V, I _C = 0V
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h _{FE}	120 60	360 —	—	I _C = -2.0mA, V _{CE} = -1.0V I _C = -50mA, V _{CE} = -1.0V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	—	-0.40	V	I _C = -50mA, I _B = -5.0mA
Base- Emitter Saturation Voltage	V _{BE(SAT)}	—	-0.95	V	I _C = -50mA, I _B = -5.0mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C _{obo}	—	4.5	pF	V _{CB} = -5.0V, f = 1.0MHz, I _E = 0
Input Capacitance	C _{ibo}	—	10	pF	V _{EB} = -0.5V, f = 1.0MHz, I _C = 0
Small Signal Current Gain	h _{fe}	120	480	—	V _{CE} = -1.0V, I _C = -2.0mA, f = 1.0kHz
Current Gain-Bandwidth Product	f _T	250	—	MHz	V _{CE} = -20V, I _C = -10mA, f = 100MHz
Noise Figure	NF	—	4.0	dB	V _{CE} = -5.0V, I _C = -100μA, R _S = 1.0kΩ, f = 1.0kHz

Notes: 3. Pulse test: Pulse width ≤ 300μs, duty cycle ≤ 2%.